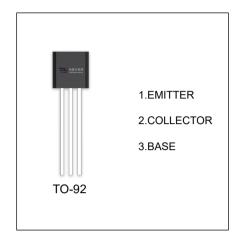


KTA1266 TRANSISTOR (PNP)

FEATURES

- Excellent h_{FE} Linearity
- Low Noise
- Complementary to KTC3198



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
KTA1266	TO-92	Bulk	1000pcs/Bag
KTA1266-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-50	V
V _{CEO}	Collector-Emitter Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-5	V
Ic	Collector Current -Continuous	-150	mA
P _D	Collector Power Dissipation	625	mW
R ₀ JA	Thermal Resistance from Junction to Ambient	200	°C /W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C



T_a =25 $^{\circ}$ C unless otherwise specified

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-50V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-0.1	μA
DC current acin	h _{FE(1)}	V_{CE} =-6V, I_{C} =-2mA	70		400	
DC current gain	h _{FE(2)}	V _{CE} =-6V, I _C =-150mA	25			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-100mA, I _B =-10mA			-0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-100mA, I _B =-10mA			-1.1	V
Transition frequency	f _T	V _{CE} =-10V, I _C =-1mA	80			MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz			7	pF
Noise figure	NF	V _{CE} =-6V, I _c =-0.1mA,		10	dB	
Noise figure		f=1KHZ, Rg=10KΩ				

CLASSIFICATION OF h_{FE(1)}

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Rank	0	Y	GR
Range	70-140	120-240	200-400